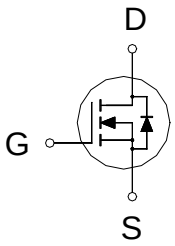
杰力科技股份有限公司
Excelliance MOS Corporation

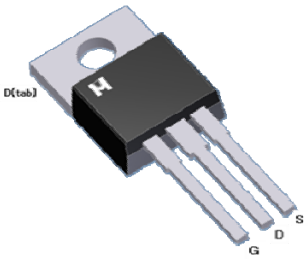
EMD02N06E

N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	60V
$R_{DSON\ (MAX.)}$	3.1mΩ
I_D	191A





UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current	T_C = 25 °C	I_D	191	A
	T_C = 100 °C		134	
Pulsed Drain Current[1]		I_{DM}	540	
Avalanche Current		I_{AS}	90	
Avalanche Energy	L = 0.1mH, ID=90A, RG=25Ω	E_{AS}	405	mJ
Repetitive Avalanche Energy[2]	L = 0.05mH	E_{AR}	202	
Power Dissipation	T_C = 25 °C	P_D	277	W
	T_C = 100 °C		111	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

100% UIS testing in condition of V_D=30V, L=0.1mH, V_G=10V, I_L=60A, Rated V_{DS}=60V N-CH

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		0.45	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

[1]Pulse width limited by maximum junction temperature.

[2]Duty cycle ≤ 1%

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2	3	4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±30V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 48V, V_{GS} = 0V			1	μA
		V_{DS} = 40V, V_{GS} = 0V, T_J = 125 °C			25	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 10V, V_{GS} = 10V	191			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 50A		2.8	3.1	mΩ
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 20A		62		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 30V, f = 1MHz		7935		pF
Output Capacitance	C_{oss}			1082		
Reverse Transfer Capacitance	C_{rss}			248		
Gate Resistance	R_g	V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz		1.7		Ω
Total Gate Charge[1,2]	Q_g	V_{DS} = 30V, V_{GS} = 10V, I_D = 20A		91		nC
Gate-Source Charge[1,2]	Q_{gs}			50		
Gate-Drain Charge[1,2]	Q_{gd}			16		
Turn-On Delay Time[1,2]	$t_{d(on)}$	V_{DS} = 30V, I_D = 20A, V_{GS} = 10V, R_{GS} = 6Ω		100		nS
Rise Time[1,2]	t_r			180		
Turn-Off Delay Time[1,2]	$t_{d(off)}$			110		
Fall Time[1,2]	t_f			200		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25 °C)						
Continuous Current	I_S				191	A
Pulsed Current[3]	I_{SM}				540	
Forward Voltage[1]	V_{SD}	I_F = 50A, V_{GS} = 0V			1.3	V
Reverse Recovery Time	t_{rr}	I_F = 20A, dI_F/dt = 100A / μS		36		nS
Reverse Recovery Charge	Q_{rr}			280		nC

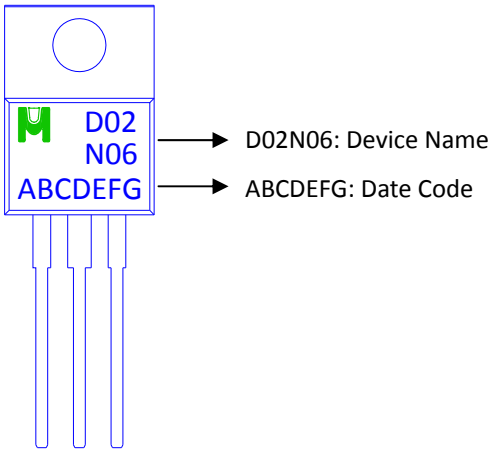
[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

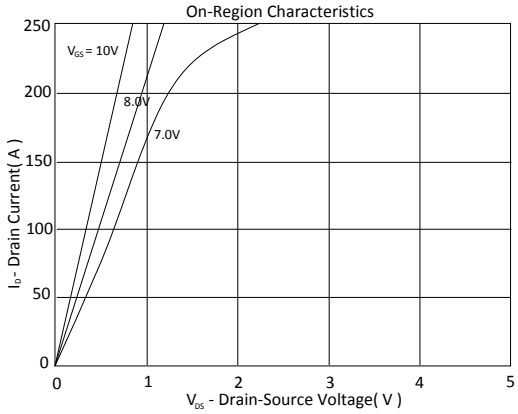
[3]Pulse width limited by maximum junction temperature.

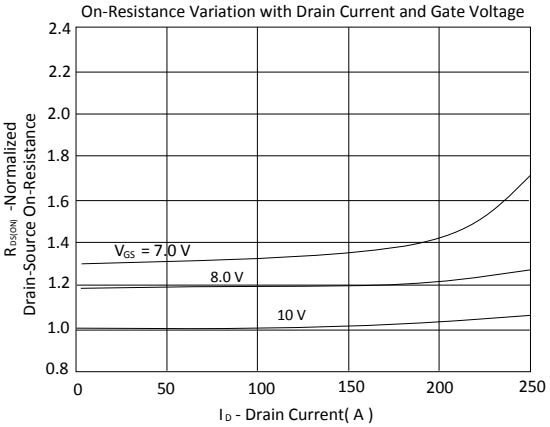
Ordering & Marking Information:

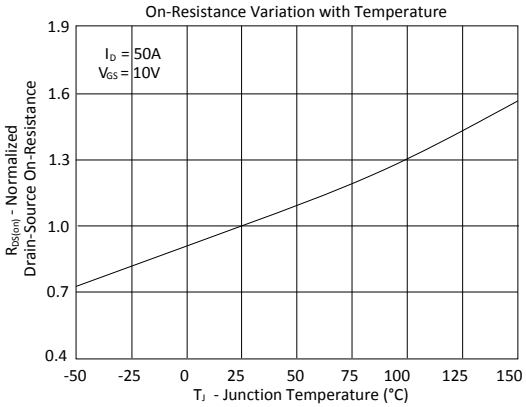
Device Name: EMD02N06E for TO-220

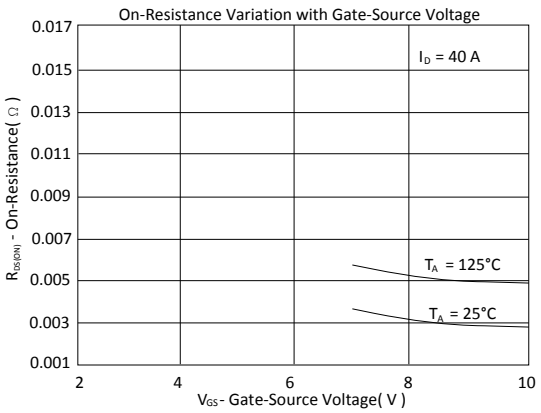


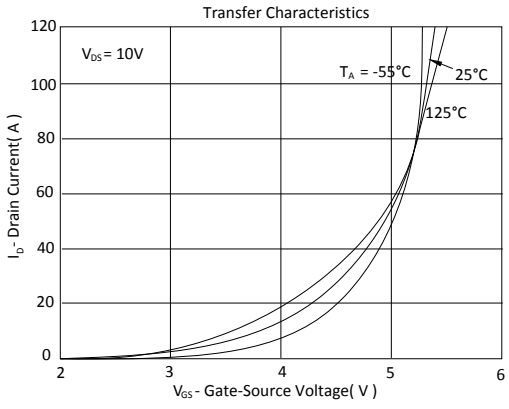
TYPICAL CHARACTERISTICS

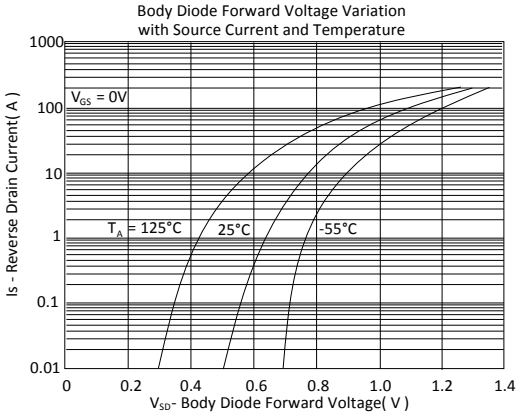


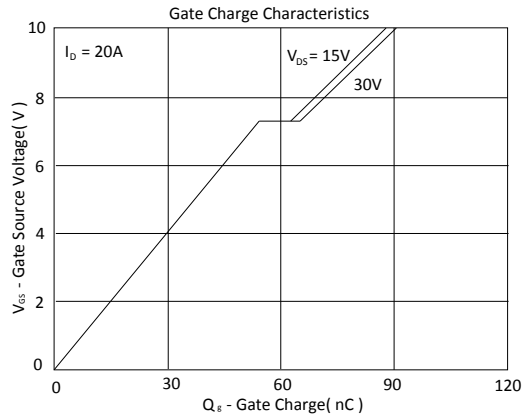


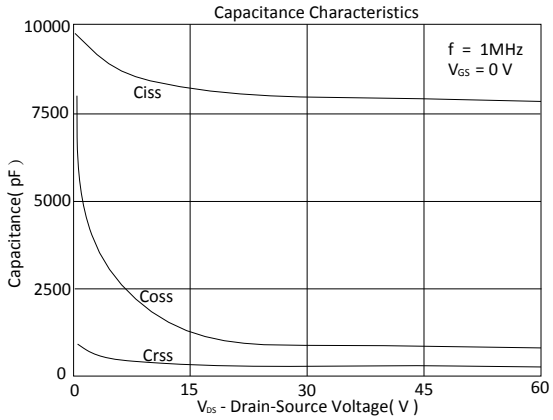


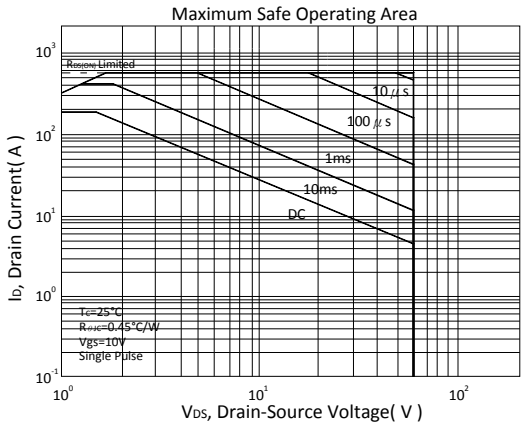


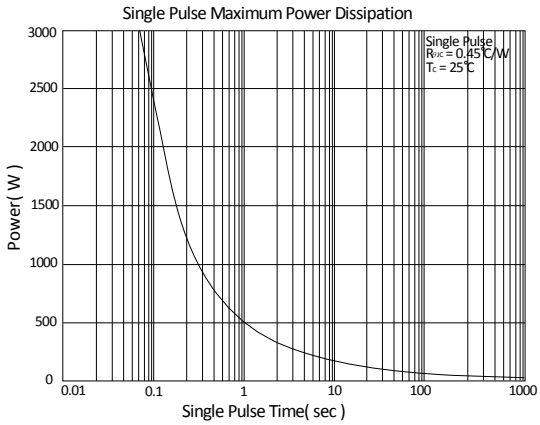


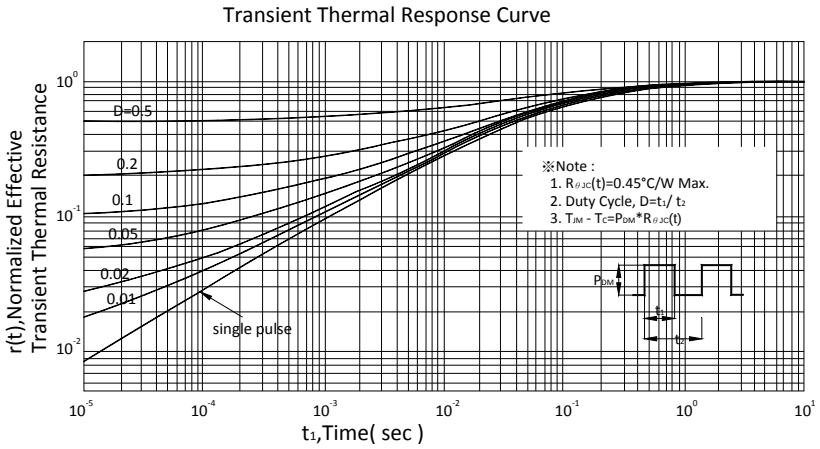



Gate Charge Characteristics
I_D = 20A
V_{DS}= 15V
30V
V_{GS} - Gate Source Voltage(V)
Q_g - Gate Charge(nC)

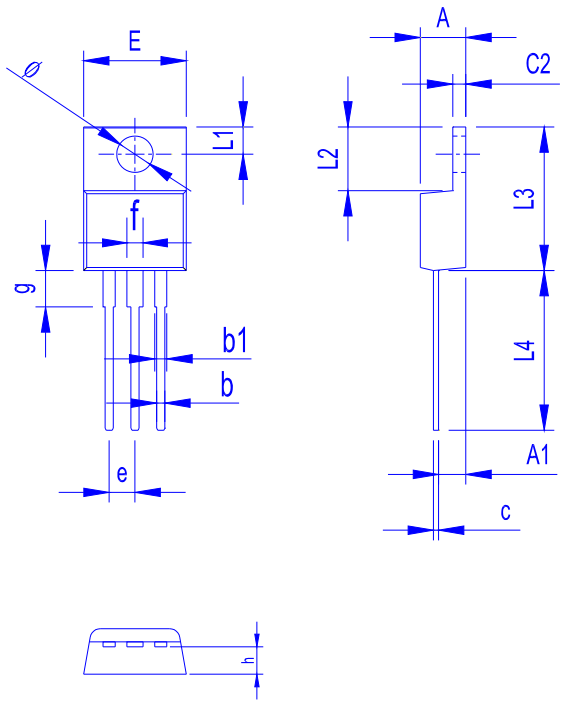

Capacitance Characteristics
f = 1MHz
V_{GS} = 0 V
Ciss
Coss
Crss
Capacitance(pF)
V_{DS} - Drain-Source Voltage(V)


Maximum Safe Operating Area
$R_{DS(ON)}$ Limited
10 μs
100 μs
1ms
10ms
DC
T_C=25°C
$R_{\theta JC}$=0.45°C/W
Vgs=10V
Single Pulse
I_D, Drain Current(A)
V_{DS}, Drain-Source Voltage(V)


Single Pulse Maximum Power Dissipation
Single Pulse
$R_{\theta JC}$ = 0.45°C/W
T_C = 25°C
Power(W)
Single Pulse Time(sec)


Transient Thermal Response Curve
D=0.5
0.2
0.1
0.05
0.02
0.01
single pulse
※Note :
1. $R_{\theta JC}$(t)=0.45°C/W Max.
2. Duty Cycle, D=t_1/ t_2
3. T_{JM} - T_C=P_{DM}*$R_{\theta JC}$(t)
P_{DM}
t_1
t_2
r(t),Normalized Effective Transient Thermal Resistance
t_1,Time(sec)

Outline Drawing



Dimension in mm

Dimension	A	b	b1	c	c2	E	L1	L2	L3	L4	ø	e	f	g	h
Min.	4.20	0.70	0.90	0.30	1.10	9.80	2.55	6.10	14.80	13.50	3.40	2.35	1.30	3.40	2.40
Max.	4.80	1.10	1.50	0.70	1.50	10.50	2.85	6.50	15.40	14.50	3.80	2.75	1.90	3.80	3.00